



DMG4800LFG

#### N-CHANNEL ENHANCEMENT MODE MOSFET

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

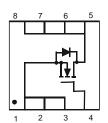
- Case: DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.0172 grams (approximate)



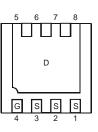


TOP VIEW

BOTTOM VIEW



TOP VIEW Internal Schematic



BOTTOM VIEW Pin Configuration

#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Charac	teristic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Drain Current (Note 3)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	۱ <sub>D</sub>	7.44 4.82	А
Pulsed Drain Current (Note 4)			I <sub>DM</sub>	40	A

### **Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	PD	0.94	W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	133	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

3. Device mounted on FR-4 PCB with minimum recommended pad layout.

4. Repetitive rating, pulse width limited by junction temperature.

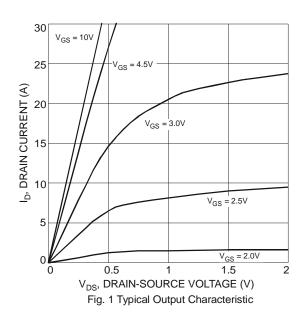


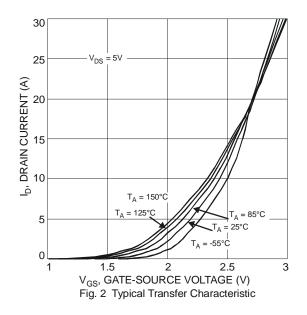
# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

			-				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)	i						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current TJ = 25°C	I <sub>DSS</sub>	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	-	1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Statia Drain Sauras On Desintance	0	- 11 - 15	17	17	$V_{GS} = 10V, I_D = 9A$		
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		15	24	mΩ	$V_{GS} = 4.5V, I_D = 7A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	8	-	S	$V_{DS} = 10V, I_{D} = 9A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C <sub>iss</sub>	-	798	-	pF	$-V_{DS} = 10V, V_{GS} = 0V,$ -f = 1.0MHz	
Output Capacitance	Coss	-	128	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	122	-	pF	-1 = 1.0MHz	
Gate Resistance	R <sub>g</sub>	-	1.37	-	Ω	$V_{DS}$ =0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge	Qg	-	9.47	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	1.87	-	nC	− V <sub>GS</sub> = 5V, V <sub>DS</sub> = 15V, − I <sub>D</sub> = 9A	
Gate-Drain Charge	Q <sub>gd</sub>	-	5.60	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.03	-	ns	V <sub>DD</sub> = 15V, V <sub>GEN</sub> = 10V, R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 1A	
Turn-On Rise Time	tr	-	4.50	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	26.33	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	8.55	-	ns	]	

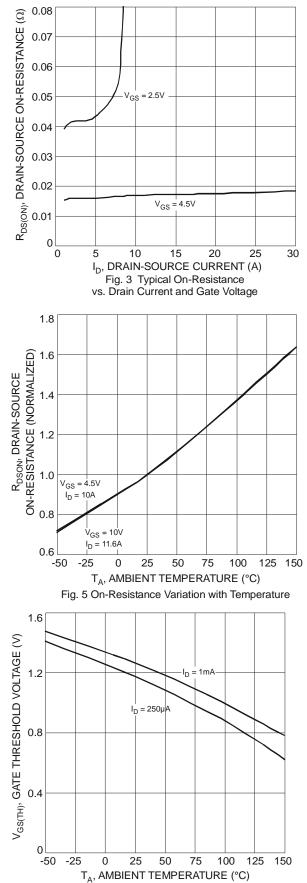
Notes: 5. Short duration pulse test used to minimize self-heating effect.

6. Guaranteed by design. Not subject to product testing.











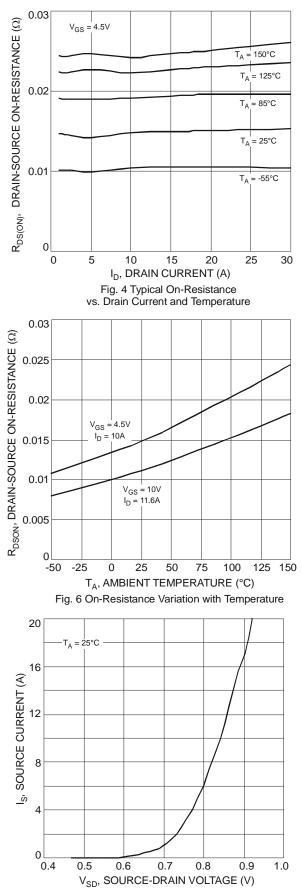
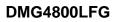
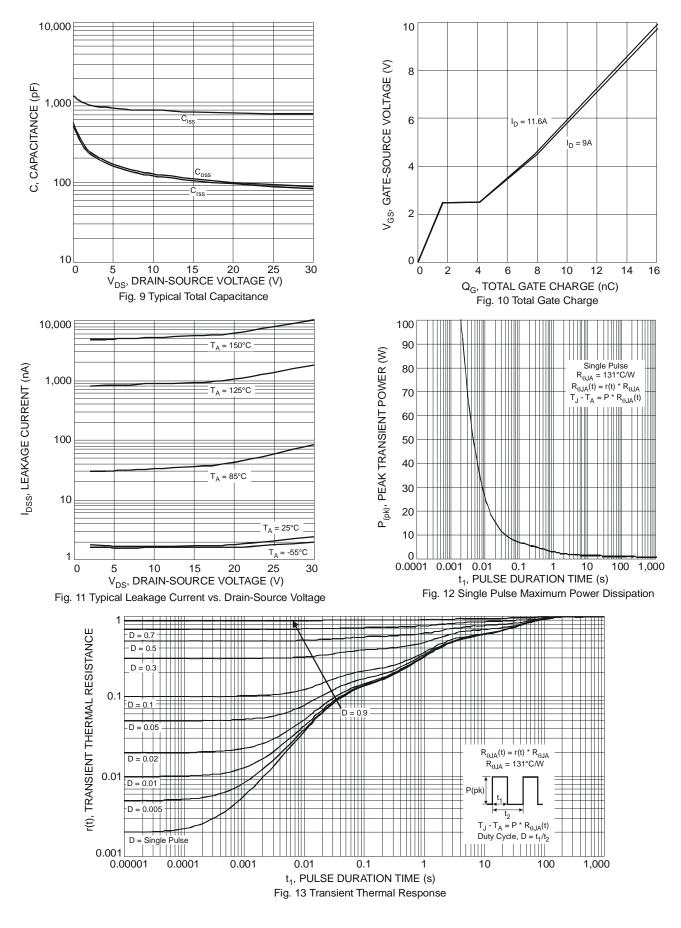


Fig. 8 Diode Forward Voltage vs. Current







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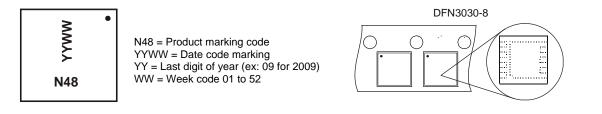


## Ordering Information (Note 7)

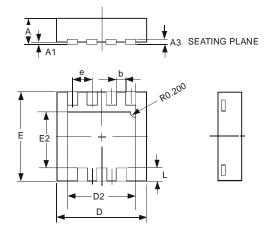
Part Number	Case	Packaging
DMG4800LFG-7	DFN3030-8	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**

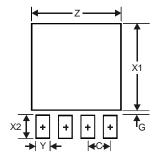


# **Package Outline Dimensions**



DFN3030-8				
Dim	Min	Max	Тур	
Α	0.57	0.63	0.60	
A1	0	0.05	0.02	
A3	_	_	0.15	
b	0.29	0.39	0.34	
D	2.90	3.10	3.00	
D2	2.19	2.39	2.29	
е			0.65	
Е	2.90	3.10	3.00	
E2	1.64	1.84	1.74	
Ĺ	0.30	0.60	0.45	
All Dimensions in mm				

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Y	0.39
C	0.65



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